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Gehrke et al.

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(54) **PENDEOEPITAXIAL METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS ON SAPPHIRE SUBSTRATES, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY**

(58) **Field of Classification Search** 438/41, 438/46, 478, 479, 481, 483, 484, 492, 604, 438/503, 507; 117/97, 952
See application file for complete search history.

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